

Abstract of the Disclosure:

A method for correcting local loading-effects in photomask etching includes the steps of determining the location-dependent density of structures of a mask; determining the
5 location-dependent strength of the loading effect with the aid of the structure density; and determining location-dependent correction values for the mask structures with the aid of the strength of the loading effect for the purpose of compensating the loading effect. It is recognized that the strength of
10 location-dependent loading effects can be predicted with the aid of the location-dependent structure density and therefore compensated.

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